
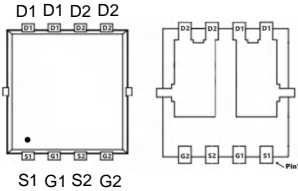




TM30V03DF

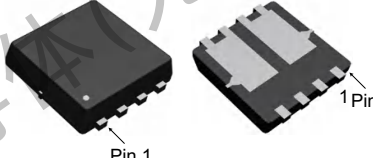
P+P-Channel Enhancement Mode Mosfet

<p>General Description</p> <ul style="list-style-type: none"> • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM 	<p>General Features</p> <p>$V_{DS} = -30V$ $I_D = -30A$</p> <p>$R_{DS(ON)} = 12m\Omega$(typ.) @ $V_{GS} = -10V$</p> <p>100% UIS Tested 100% R_g Tested</p> 
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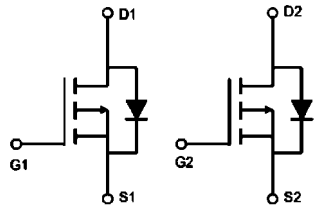


Marking:30V03

DF:DFN3x3-8L



Pin 1



Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-30	A
$I_D @ T_A = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-17.5	A
I_{DM}	Pulsed Drain Current	-100	A
EAS	Single Pulse Avalanche Energy	25	mJ
I_{AS}	Avalanche Current	---	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	28	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	---	60	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	4.5	$^\circ C/W$



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Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu\text{A}$	-30	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=-30V$	---	---	-1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu\text{A}$	-1	-1.5	-2	V
$R_{DS(ON)}$	Drain-Source On Resistance	$V_{GS}=-10V, I_D=-10A$	---	12	15	m Ω
		$V_{GS}=-4.5V, I_D=-5A$	---	18	23	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$	---	1300	---	pF
C_{oss}	Output Capacitance		---	159	---	
C_{rss}	Reverse Transfer Capacitance		---	144	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V$ $R_{GEN}=3\ \Omega, V_{GS}=-10V$	---	17	---	ns
t_r	Rise Time		---	21	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	54	---	ns
t_f	Fall Time		---	41	---	ns
Q_g	Total Gate Charge		$V_{GS}=-10V, V_{DS}=-15V,$ $I_D=-10A$	---	26	---
Q_{gs}	Gate-Source Charge	---		5	---	nC
Q_{gd}	Gate-Drain "Miller" Charge	---		4.2	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=-1A$	---	-0.75	-1	V
I_S	Diode Forward Current	$V_D=V_G=0V$	---	---	-30	A
I_{SM}	Pulsed Source Current	$V_D=V_G=0V$	---	---	-100	A
T_{rr}	Reverse Recovery Time	$I_S=-10A, di/dt=100A/\mu\text{s},$ $T_J=25^\circ\text{C}$	---	32	---	ns
Q_{rr}	Reverse Recovery Charge		---	28	---	nC



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Typical Characteristics: ($T_c=25^\circ\text{C}$ unless otherwise noted)

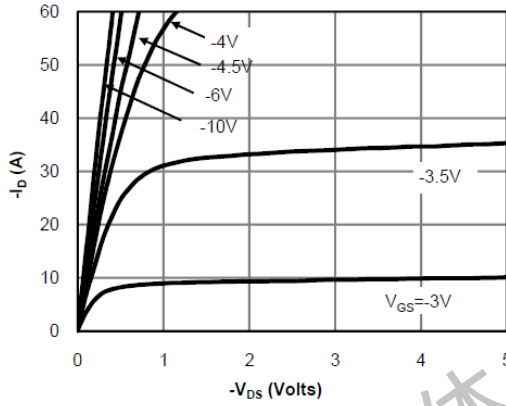


Figure 1. On-Regin Characteristics

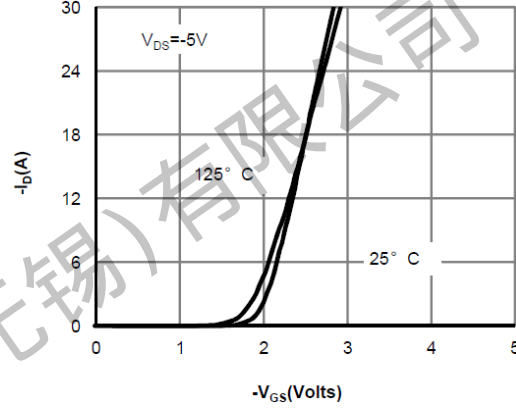


Figure 2. Transfer Characteristics

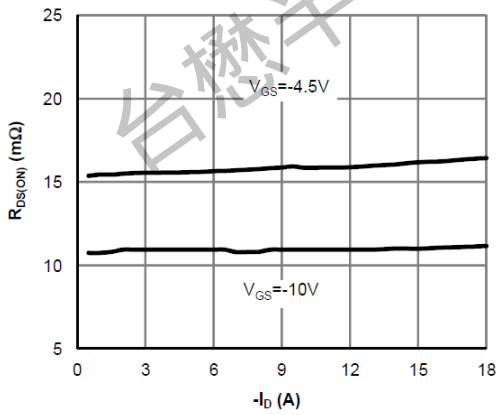


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

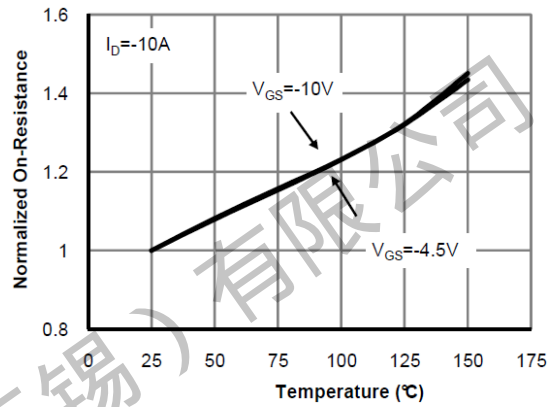


Figure 4. On-Resistance vs. Junction Temperature

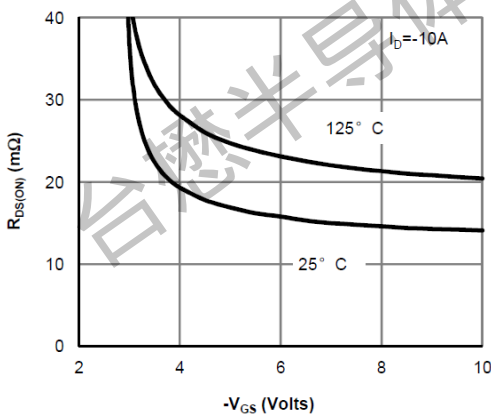


Figure 5. On-Resistance vs. Gate-Source Voltage

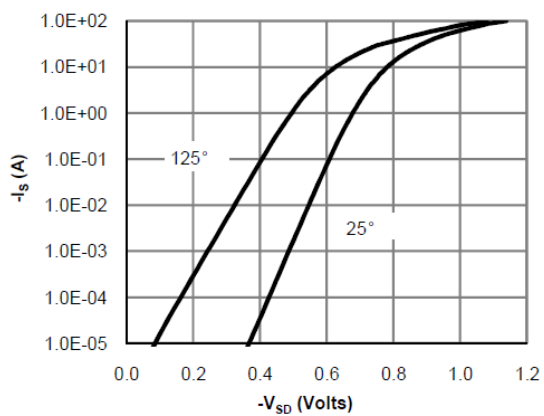


Figure 6. Body-Diode Characteristics

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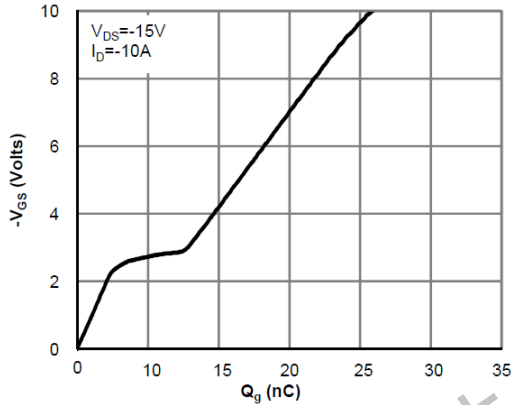


Figure 7. Gate-Charge Characteristics

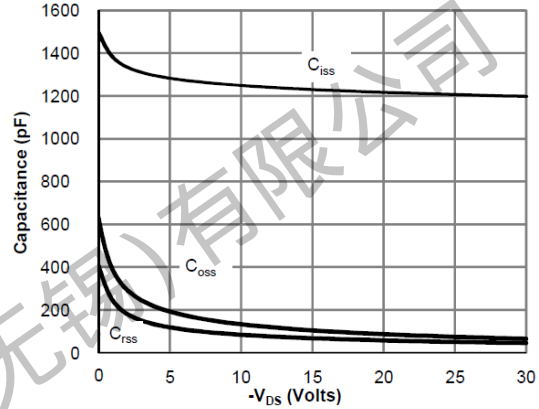


Figure 8. Capacitance Characteristics

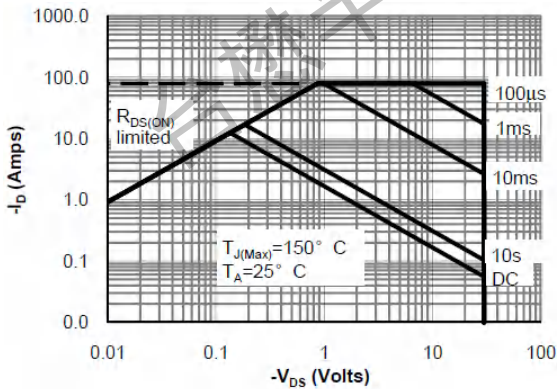


Figure 9. Maximum Forward Biased Safe Operating Area

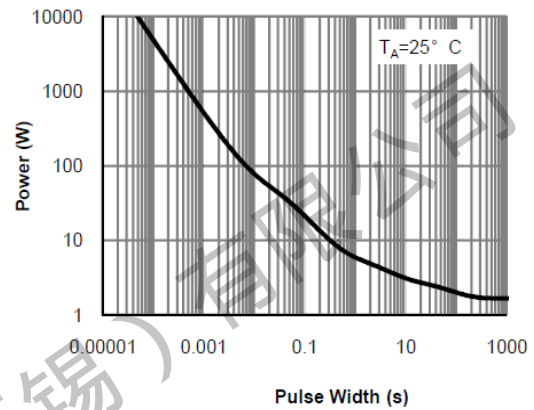


Figure 10. Single Pulse Power Rating Junction-to-Ambient

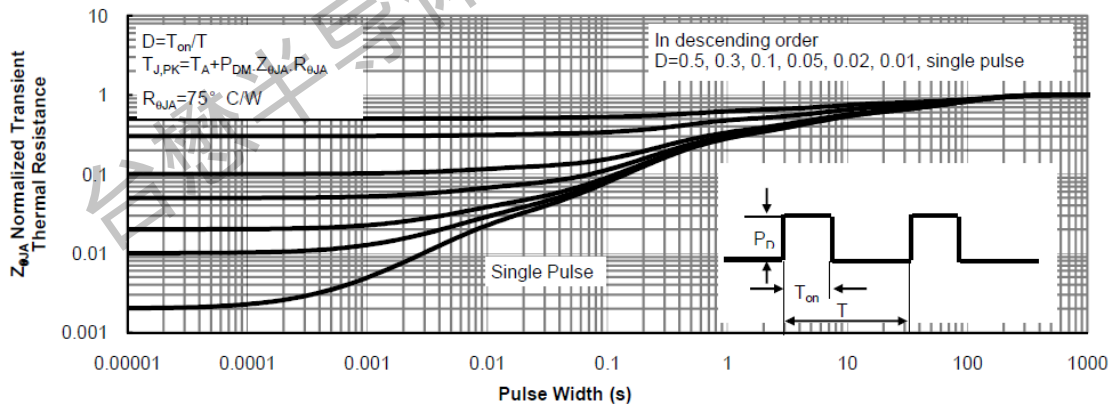


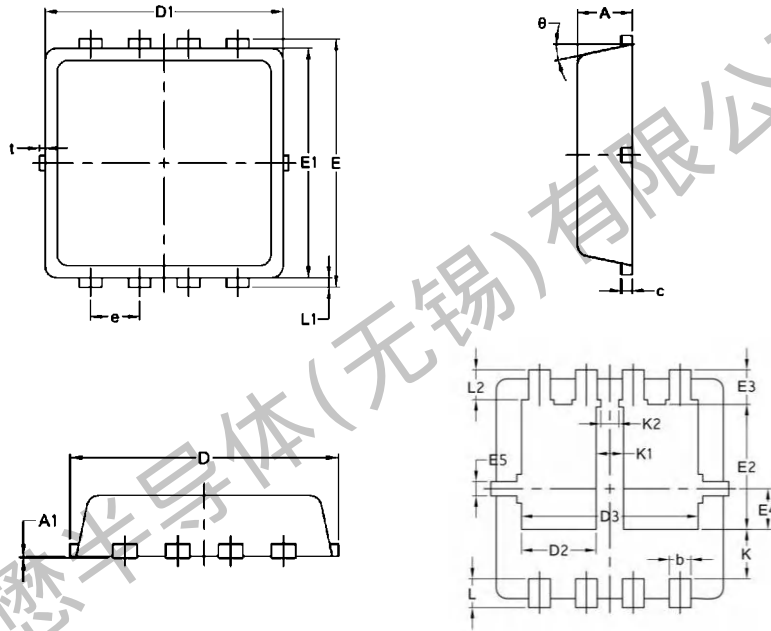
Figure 11. Normalized Maximum Transient Thermal Impedance



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Package Mechanical Data:DFN3x3-8L

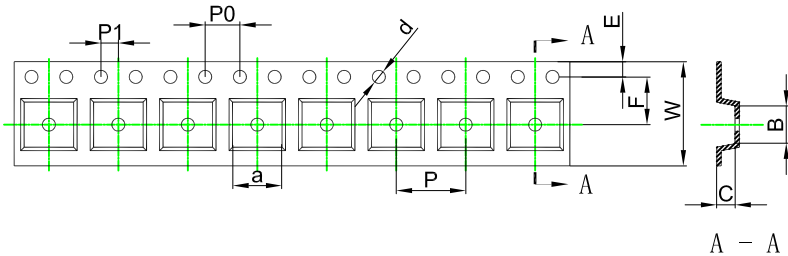


Symbol	Common		
	Mm		
	Min	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.25	0.30	0.39
c	0.14	0.152	0.20
D	3.20	3.30	3.45
D1	3.05	3.15	3.25
D2	0.84	1.04	1.24
D3	2.30	2.45	2.60
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.60	1.74	1.90
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.50	0.69	0.80
K1	0.30	0.38	0.53
K2	0.15	0.25	0.35
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
L2	0.27	0.42	0.57
t	0	0.075	0.13
Φ	10°	12°	14°

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PDFN3x3-8L Embossed Carrier Tape



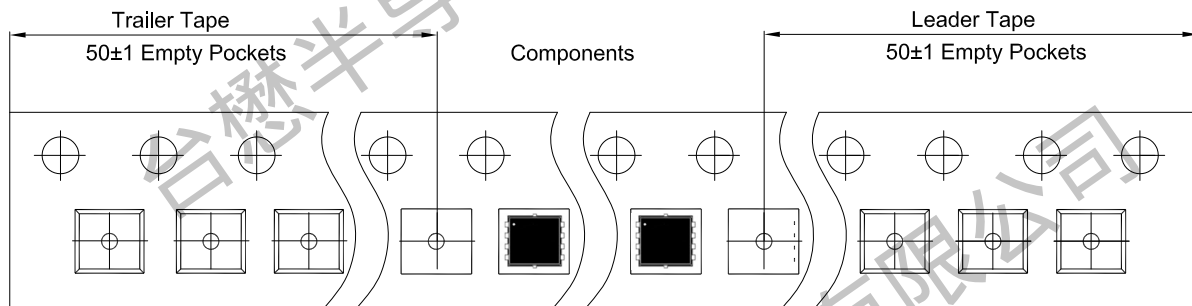
Packaging Description:

SOP-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

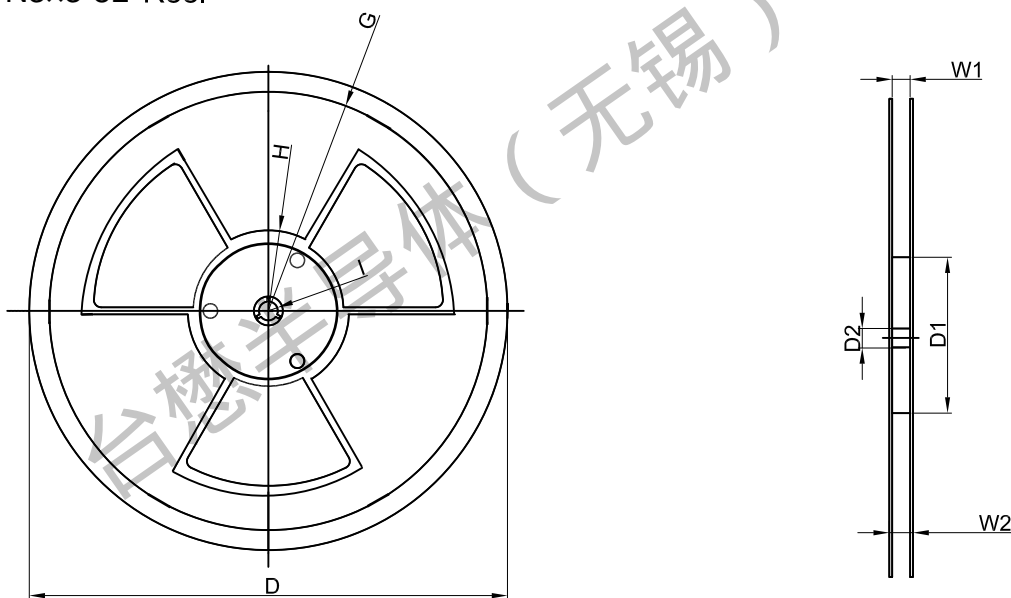
ALL DIM IN mm

Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
PDFN3x3-8L	6.40	5.40	2.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFN3x3-8L Tape Leader and Trailer



PDFN3x3-8L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
13" Dia	Ø330.00	100.00	13.00	R135.00	R55.00	R6.50	12.00	14.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
5,000 pcs	13 inch	10,000 pcs	370×355×52	50,000 pcs	400×360×368	

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Revision history:

Date	Rev	Description	Page
2023.05.14	23.05	Original	